

# 4V Drive Nch+Nch MOSFET

### **SH8K32**

#### Structure

Silicon N-channel MOSFET

#### Features

- 1) Built-in G-S Protection Diode.
- 2) Small surface Mount Package (SOP8).

#### Application

Switching

#### Packaging specifications

	Package	Taping
Туре	Code	TB
	Basic ordering unit (pieces)	2500
SH8K32		0

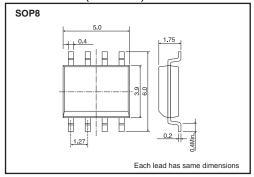
#### ●Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2.>

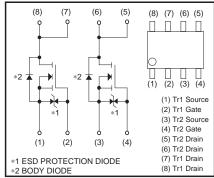
Parameter		Symbol	Limits	Unit
Drain-source voltage		V <sub>DSS</sub>	60	V
Gate-source voltage		V <sub>GSS</sub>	±20	V
Drain current	Continuous	I <sub>D</sub>	±4.5	Α
	Pulsed	I <sub>DP</sub> *1	±18	Α
Source current (Body diode)	Continuous	Is	1.0	Α
	Pulsed	I <sub>SP</sub> *1	18	Α
Total power dissipation		P <sub>D</sub> *2	2.0	W/TOTAL
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

<sup>\*1</sup> Pw≤10µs, Duty cycle≤1% \*2 Mounted on a ceramic board.

#### ●Dimensions (Unit: mm)



#### ●Inner circuit



\*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

**SH8K32 Data Sheet** 

●Electrical characteristics (Ta=25°C) <It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	-	-	±10	μΑ	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)</sub> DSS	60	_	_	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	_	_	1	μА	VDS= 60V, VGS=0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	-	2.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state resistance	RDS (on)*	_	46	65	mΩ	I <sub>D</sub> = 4.5A, V <sub>G</sub> S= 10V
		_	52	73	mΩ	I <sub>D</sub> = 4.5A, V <sub>GS</sub> = 4.5V
		_	55	77	mΩ	ID= 4.5A, VGS= 4.0V
Forward transfer admittance	Y <sub>fs</sub> *	4.0	_	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 4.5A
Input capacitance	Ciss	-	500	-	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	-	120	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	_	55	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	12	_	ns	Vpp≒ 30V
Rise time	tr *	-	18	_	ns	ID= 2.3A   VGS= 10V
Turn-off delay time	t <sub>d (off)</sub> *	-	40	-	ns	$R_{L}=13\Omega$
Fall time	t <sub>f</sub> *	_	13	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	-	7.0	10	nC	V <sub>DD</sub> ≒30V, V <sub>GS</sub> =5V
Gate-source charge	Q <sub>gs</sub> *	-	1.6	-	nC	I <sub>D</sub> = 4.5A
Gate-drain charge	Q <sub>gd</sub> *	_	2.5	-	nC	$R_L=6.7\Omega$ , $R_G=10\Omega$

<sup>\*</sup>Pulsed

#### ●Body diode characteristics (Source-Drain) (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V <sub>SD</sub> *	_	_	1.2	V	I <sub>S</sub> =4.5A, V <sub>GS</sub> =0V

<sup>\*</sup>Pulsed

SH8K32 Data Sheet

#### •Electrical characteristic curves

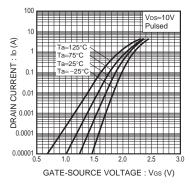


Fig.1 Typical Transfer Characteristics

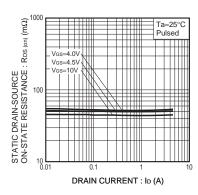


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current(I)

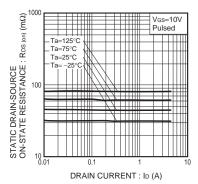


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current(II)

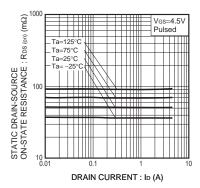


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(III)

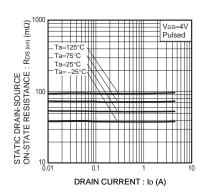


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(IV)

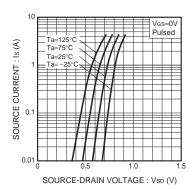


Fig.6 Source Current vs. Source-Drain Voltage

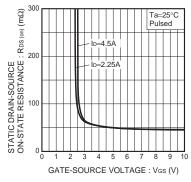


Fig.7 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

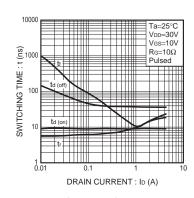


Fig.8 Switching Characteristics

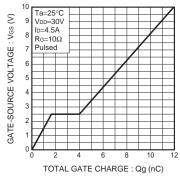


Fig.9 Dynamic Input Characteristics

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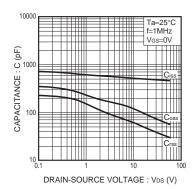


Fig.10 Typical Capacitance vs. Drain-Source Voltage

#### Measurement circuits

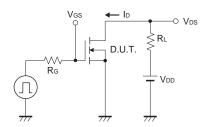


Fig.1-1 Switching Time Test Circuit

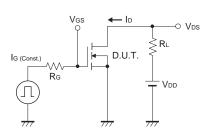


Fig.2-1 Gate Charge Test Circuit

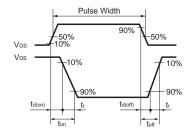


Fig.1-2 Switching Time Waveforms

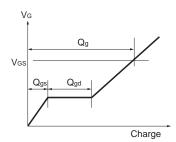


Fig.2-2 Gate Charge Waveform

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